Electronic Supplementary Information

Room-Temperature Solution-Processed Molybdenum Oxide as Hole Transport Layer with Ag Nanoparticles for Highly **Efficient Inverted Organic Solar Cells**

Xinchen Li,^a Wallace Chikho Choy,*^a Fengxian Xie,^a Shaoqing Zhang^b and Jianhui Hou^b

^a Department of Electrical and Electronic Engineering, The University of Hong Kong, Pokfulam Road, Hong Kong, China. ^b Institute of Chemistry, Chinese Academy of Sciences, Beijing 100190, China. * Corresponding author: chchoy@eee.hku.hk (Choy)



Fig. S1 J-V characteristics of P3HT:PCBM OSCs with different thicknesses of solution-processed MoO_x interfacial layer.



Fig. S2 The plot of $(\alpha hv)^{1/2}$ verse photon energy (hv) of pristine MoO_x, where α is absorption coefficient. The intersection of tangent with energy axis is the E_{opt}.



Fig. S3 IPCE spectra of P3HT:PCBM OSCs with thermally evaporated MoO_3 film (black line) and solution-processed MoO_x film (red line).



Fig. S4 J_{dark} -V characteristics of P3HT:PCBM OSCs with different weight ratios of Ag NPs in the Ag NP-MoO_x composite film.



Fig. S5 J_{dark} -V characteristics of PBDTTT-C-T:PC₇₁BM OSCs with different weight ratios of Ag NPs in the Ag NP-MoO_x composite film.



Fig. S6 IPCE spectra of PBDTTT-C-T:PC₇₁BM OSCs with different MoO_x interfacial layers.



Fig. S7 J-V characteristics of hole dominated devices with evaporated MoO₃ film, pristine MoO_x film and Ag NP-MoO_x composite film. The device structure is ITO/ PEDOT:PSS/P3HT:PCBM/MoO_x/Ag.



Fig. S8 TPV of P3HT:PCBM OSCs with evaporated MoO_3 film, pristine MoO_x film and Ag NP-MoO_x composite film. The device structure is ITO/TiO₂/P3HT:PCBM/ MoO_x /Ag.



Fig. S9 Field-emission scanning electron microscope (FE-SEM) images of (a) pristine MoO_x coated onto P3HT:PCBM blend active layer, (b) Ag NP-MoO_x composite film coated onto P3HT:PCBM blend active layer. The scale bars are 100 nm. The arrows point out some of the silver nanoparticles in the composite film.